

# Low Noise, JFET Input Operational Amplifiers

These low noise JFET input operational amplifiers combine two state-of-the-art analog technologies on a single monolithic integrated circuit. Each internally compensated operational amplifier has well matched high voltage JFET input device for low input offset voltage. The BIFET technology provides wide bandwidths and fast slew rates with low input bias currents, input offset currents, and supply currents. Moreover, the devices exhibit low noise and low harmonic distortion, making them ideal for use in high fidelity audio amplifier applications.

These devices are available in single, dual and quad operational amplifiers which are pin-compatible with the industry standard MC1741, MC1458, and the MC3403/LM324 bipolar products.

Low Input Noise Voltage: 18 nV/√Hz Typ
 Low Harmonic Distortion: 0.01% Typ
 Low Input Bias and Offset Currents
 High Input Impedance: 10<sup>12</sup> Ω Typ
 High Slew Rate: 13 V/xs Typ

Wide Gain Bandwidth: 4.0 MHz Typ
Low Supply Current: 1.4 mA per Amp

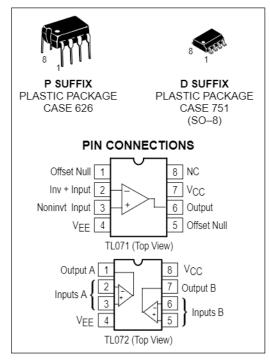
#### ORDERING INFORMATION

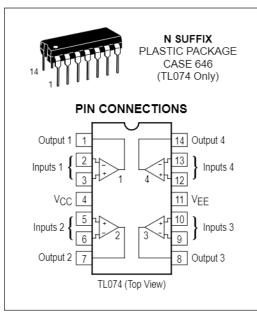
Op Amp Function	Device	Operating Temperature Range	Package
Single	TL071CD	T <sub>A</sub> = 0° to +70°C	SO-8
Siligie	TL071ACP	1A - 0 10 170 C	Plastic DIP
Dual	TL072CD	T <sub>A</sub> = 0° to +70°C	SO-8
Duai	TL072ACP	1A-0 10 170 C	Plastic DIP
Quad	TL074CN, ACN	T <sub>A</sub> = 0° to +70°C	Plastic DIP

# TL071C,AC TL072C,AC TL074C.AC

### LOW NOISE, JFET INPUT OPERATIONAL AMPLIFIERS

SEMICONDUCTOR TECHNICAL DATA





#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Supply Voltage	V <sub>CC</sub> V <sub>EE</sub>	18 –18	V
Differential Input Voltage	V <sub>ID</sub>	±30	V
Input Voltage Range (Note 1)	V <sub>IDR</sub>	±15	V
Output Short Circuit Duration (Note 2)	tsc	Continuous	
Power Dissipation Plastic Package (N, P) Derate above T <sub>A</sub> = 47°C	P <sub>D</sub> 1.0/θ <sub>JA</sub>	680 10	mW mW/°C
Operating Ambient Temperature Range	TA	0 to +70	°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C

**NOTES:** 1. The magnitude of the input voltage must not exceed the magnitude of the supply voltage or 15 V, whichever is less.

## **ELECTRICAL CHARACTERISTICS** ( $V_{CC} = 15 \text{ V}$ , $V_{EE} = -15 \text{ V}$ , $T_{A} = T_{high}$ to $T_{low}$ [Note 1])

Characteristics	Symbol	Min	Тур	Max	Unit
Input Offset Voltage (R <sub>S</sub> ≤ 10 k, V <sub>CM</sub> = 0)	V <sub>IO</sub>				mV
TL071C, TL072C		-	-	13	
TL074C		-	-	13	
TL07_AC		_	-	7.5	
Input Offset Current (V <sub>CM</sub> = 0) (Note 2)	IIO				nA
TL07_C		-	-	2.0	
TL07_AC		_	_	2.0	
Input Bias Current (V <sub>CM</sub> = 0) (Note 2)	Ι <sub>ΙΒ</sub>				nA
TL07_C		-	-	7.0	
TL07_AC		-	-	7.0	
Large–Signal Voltage Gain (V <sub>O</sub> = ±10 V, R <sub>I</sub> ≥ 2.0 k)	Avol				V/mV
TL07_C		15	-	-	
TL07_AC		25	-	-	
Output Voltage Swing (Peak-to-Peak)	Vo				V
(R <sub>L</sub> ≥ 10 k)		24	-	-	
$(R_L \ge 2.0 \text{ k})$		20	-	-	

NOTES: 1. T<sub>IOW</sub> = 0°C for TL071C,AC TL072C,AC TL074C,AC TL074C,AC TL074C,AC TL074C,AC

Figure 1. Unity Gain Voltage Follower

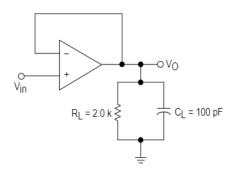
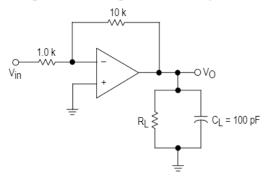


Figure 2. Inverting Gain of 10 Amplifier



The output may be shorted to ground or either supply. Temperature and/or supply voltages must be limited to ensure that power dissipation ratings are not exceeded.

<sup>3.</sup> ESD data available upon request.

<sup>2.</sup> Input Bias currents of JFET input op amps approximately double for every 10°C rise in junction temperature as shown in Figure 3. To maintain junction temperature as close to ambient temperature as possible, pulse techniques must be used during testing.

# **ELECTRICAL CHARACTERISTICS** ( $V_{CC}$ = 15 V, $V_{EE}$ = -15 V, $T_{A}$ = 25°C, unless otherwise noted.)

Characteristics	Symbol	Min	Тур	Max	Unit
Input Offset Voltage (R <sub>S</sub> ≤ 10 k, V <sub>CM</sub> = 0) TL071C, TL072C TL074C TL07_AC	VIO	_ _ _	3.0 3.0 3.0	10 10 6.0	mV
Average Temperature Coefficient of Input Offset Voltage $R_S = 50 \Omega$ , $T_A = T_{low}$ to $T_{high}$ (Note 1)	ΔV <sub>IO</sub> /ΔΤ	-	10	-	αV/°C
Input Offset Current (V <sub>CM</sub> = 0) (Note 2) TL07_C TL07_AC	IIO	_ _	5.0 5.0	50 50	pA
Input Bias Current (V <sub>CM</sub> = 0) (Note 2) TL07_C TL07_AC	I <sub>IB</sub>	_ _	30 30	200 200	pA
Input Resistance	rį	-	1012	_	Ω
Common Mode Input Voltage Range TL07_C TL07_AC	VICR	±10 ±11	15, –12 15, –12	_ _	V
Large–Signal Voltage Gain (V <sub>O</sub> = ±10 V, R <sub>L</sub> ≥ 2.0 k) TL07_C TL07_AC	Avol	25 50	150 150	_ _	V/mV
Output Voltage Swing (Peak-to-Peak) (R <sub>L</sub> = 10 k)	Vo	24	28	-	V
Common Mode Rejection Ratio (R <sub>S</sub> ≤ 10 k) TL07_C TL07_AC	CMRR	70 80	100 100	  -  -	dB
Supply Voltage Rejection Ratio (R <sub>S</sub> ≤ 10 k) TL07_C TL07_AC	PSRR	70 80	100 100	_ _	dB
Supply Current (Each Amplifier)	ID	-	1.4	2.5	mA
Unity Gain Bandwidth	BW	-	4.0	_	MHz
Slew Rate (See Figure 1) V <sub>In</sub> = 10 V, R <sub>L</sub> = 2.0 k, C <sub>L</sub> = 100 pF	SR	-	13	-	V/œS
Rise Time (See Figure 1)	t <sub>r</sub>	-	0.1	-	αs
Overshoot ( $V_{in}$ = 20 mV, $R_L$ = 2.0 k, $C_L$ = 100 pF)	OS	-	10	-	%
Equivalent Input Noise Voltage $R_S = 100 \Omega$ , $f = 1000 Hz$	e <sub>n</sub>	-	18	-	nV/√Hz
Equivalent Input Noise Current $R_S = 100 \Omega$ , $f = 1000 Hz$	in	-	0.01	-	pA/√Hz
Total Harmonic Distortion $V_O$ (RMS) = 10 V, $R_S \le 1.0$ k, $R_L \ge 2.0$ k, $f = 1000$ Hz	THD	-	0.01	-	%
Channel Separation A <sub>V</sub> = 100	CS	-	120	-	dB

NOTES: 1. T<sub>IOW</sub> = 0°C for TL071C,AC
TL072C,AC
TL074C,AC
TL074C,AC
TL074C,AC
TL074C,AC
TL074C,AC
2. Input Bias currents of JFET input op amps approximately double for every 10°C rise in junction temperature as shown in Figure 3. To maintain junction temperature as close to ambient temperature as possible, pulse techniques must be used during testing.

Figure 3. Input Bias Current versus Temperature

100

100

VCCVEE = ±15 V

100

1.0

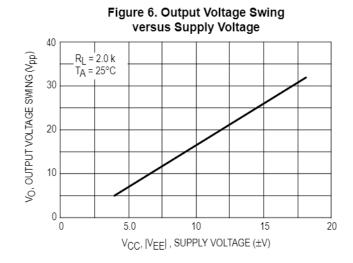
0.01

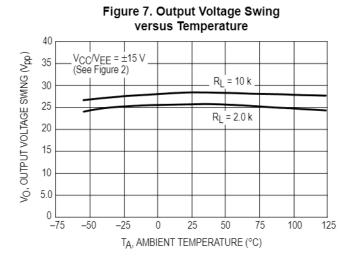
-100 -75 -50 -25 0 25 50 75 100 125 150

TA, AMBIENT TEMPERATURE (°C)

Figure 4. Output Voltage Swing versus Frequency 35 R<sub>L</sub> = 2.0 k T<sub>A</sub> = 25°C (See Figure 2) V<sub>O</sub>, OUTPUT VOLTAGE SWING (V<sub>pp</sub>) 30 25 20 15 10 5.0 0 100 1.0 k 10 k 100 k 1.0 M 10 M f, FREQUENCY (Hz)

Figure 5. Output Voltage Swing versus Load Resistance 40 Vo, OUTPUT VOLTAGE SWING (Vpp) VCC/VEE = ±15 V TA = 25°C 30 (See Figure 2) 20 0.1 0.2 0.4 0.7 1.0 2.0 4.0 7.0  $R_I$ , LOAD RESISTANCE (k $\Omega$ )





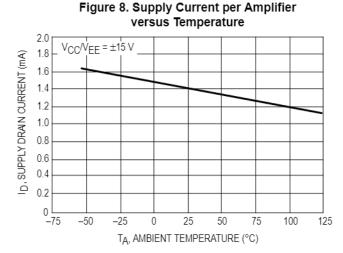
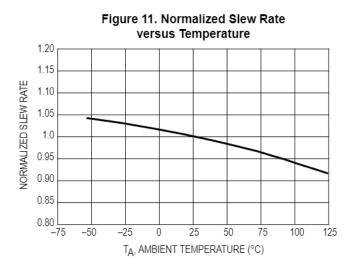
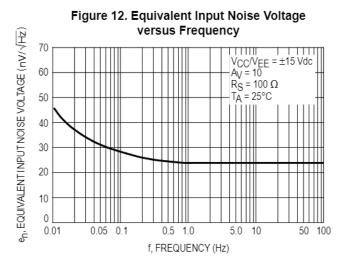
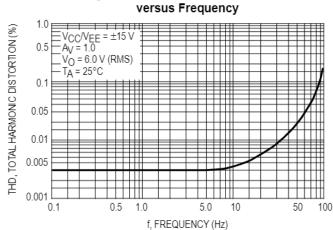


Figure 9. Large Signal Voltage Gain and Phase Shift versus Frequency 108 .VCC/VEE = ±15 V RL = 2.0 k .TA = 25°C 107 WyoL, OPEN-LOOP GAN PHASE SHFT (DEGREES 106 105 104 Gain 45° 103 102 90° Phase Shift 101 135° 180° 1.0 1.0 10 100 10 k 100 k 1.0 M 10 M f, FREQUENCY (Hz)

Figure 10. Large Signal Voltage Gain versus Temperature 1000 V<sub>CC</sub>/V<sub>EE</sub> = ±15 V = V<sub>O</sub> = ±10 V = R<sub>L</sub> = 2.0 k = WyoL, VOLTAGE GAIN (V/mV) 100 10 1.0 -75 -50 0 25 50 75 TA, AMBIENT TEMPERATURE (°C)







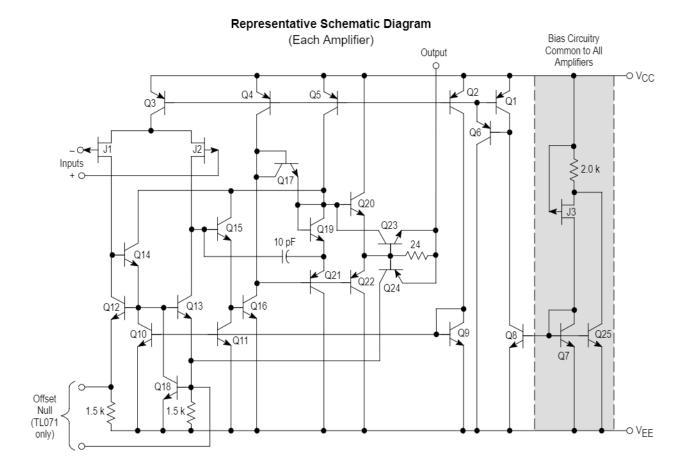


Figure 14. Audio Tone Control Amplifier

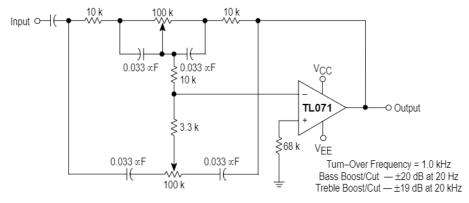
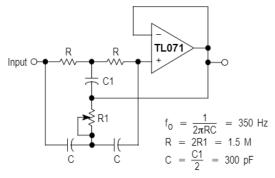
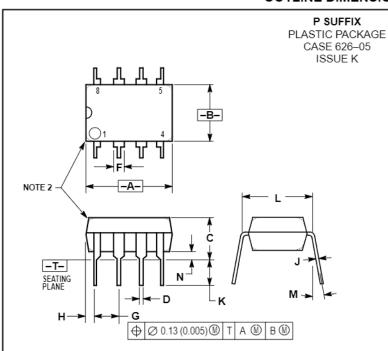


Figure 15. High Q Notch Filter

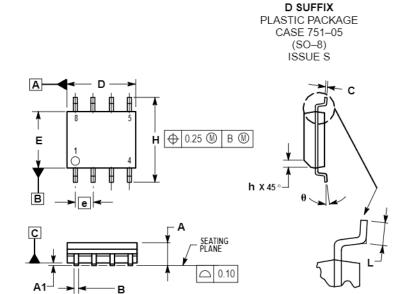


#### **OUTLINE DIMENSIONS**



- NOTES:
  1. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
  2. PACKAGE CONTOUR OPTIONAL (ROUND OR SQUARE CORNERS).
  3. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

	MILLIMETERS		INC	INCHES		
DIM	MIN	MAX	MIN	MAX		
Α	9.40	10.16	0.370	0.400		
В	6.10	6.60	0.240	0.260		
С	3.94	4.45	0.155	0.175		
D	0.38	0.51	0.015	0.020		
F	1.02	1.78	0.040	0.070		
G	2.54	BSC	0.100	BSC		
Н	0.76	1.27	0.030	0.050		
J	0.20	0.30	0.008	0.012		
K	2.92	3.43	0.115	0.135		
L	7.62	BSC	0.300	BSC		
M		10°		10°		
N	0.76	1.01	0.030	0.040		



→ 0.25 M C B S A S

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M. 1994.

  2. DIMENSIONS ARE IN MILLIMETERS.

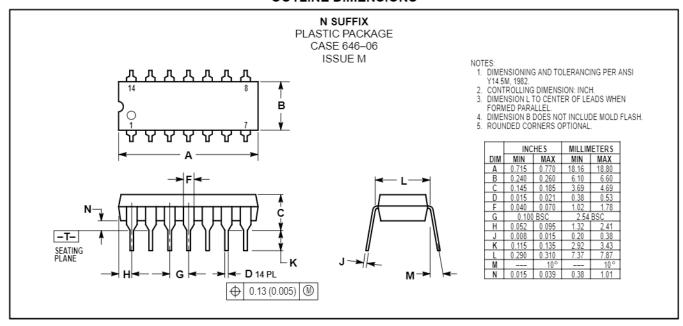
  3. DIMENSION D AND E DO NOT INCLUDE MOLD PROTRUSION.

  4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

  5. DIMENSION B DOES NOT INCLUDE MOLD PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 TOTAL IN EXCESS OF THE B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS			
DIM	MIN	MAX		
Α	1.35	1.75		
A1	0.10	0.25		
В	0.35	0.49		
С	0.18	0.25		
D	4.80	5.00		
Е	3.80	4.00		
е	1.27 BSC			
Н	5.80	6.20		
h	0.25	0.50		
L	0.40	1.25		
θ	0 °	7 º		

#### **OUTLINE DIMENSIONS**



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